

USED FOR FLUORESCENCE, DIFFRACTION, EXAFS, IMAGING AND MORE

Semiconductor Specialty Solutions for Synchrotrons





Monolithic 25 pixel detector for EXAFS application (courtesy of Dr. Uruga, SPring-8)

Comprehensive, Highly Customizable Germanium, Silicon and Si(Li) Detectors for Synchrotron Beamlines

- Monolithic Array Detectors
- ✓ Discrete Element Array Detectors
- Double Sided Strip detectors
- ✓ Nanofocused Beam Detectors
- ✓ High-Z Pixelated chips
- ✓ Single and Multi Element X-ray Silicon Detectors
- Photodiodes
- ✓ Si(Li) Detectors

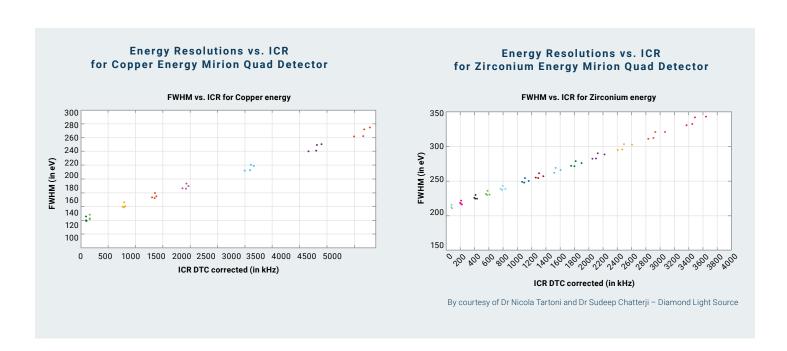




Mirion's first 13-element discrete Ge array detector, launched in the 1980s, was highly sought after by light sources like SSRL and Daresbury worldwide. Demand soon outpaced the 32-element limit, leading to the first 100-pixel monolithic detector in 1998 for Dr. Oyanagi at SPring-8, Japan.

NOW, MIRION OFFERS:

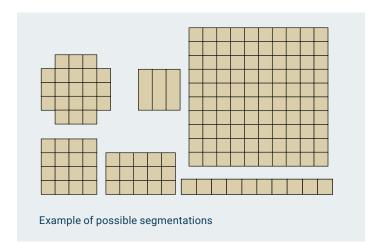
- ✓ Monolithic array detectors with 3 to 100 pixels
- ✓ Discrete array detectors up to 32 channels
- ✓ Enhanced HPGe sensors with reduced capacitance
- ✓ CMOS electronics for improved performance
- ✓ Customizable silicon drift detector arrays (since 2016), with high energy resolution and count rates (up to 3.5 Mcps)



Monolithic HPGe Pixel Detectors are based on reliable segmentation using a single planar HPGe slab. It is the only technique offering 100% beam coverage, as well as high reliability with minimal maintenance. The design allows the highest throughput electronics (up to 1 Mcps and more), and outstanding energy resolution with excellent EMI shielding.

MULTIPLE SEGMENTATION LAYOUTS

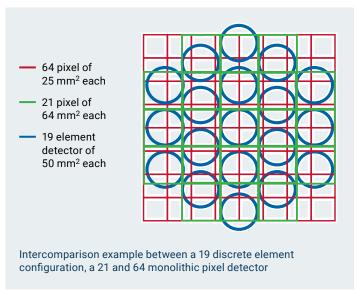
- Standard pixel sizes of 5 x 5 mm² and 8 x 8 mm²
- · Arrays from 3 to 100 pixels on a single substrate
- Standard thickness is 7 mm for energy range from 3 keV to 200 keV+



MAXIMUM BEAM COVERAGE

- · Monolithic detectors have no dead space between elements
- Optional internal collimator to reduce charge sharing between pixels and peak/background improvement
- Optional Close-To-Sample detection heads to maximize proximity in a narrow, confined space





HIGHEST RELIABILITY

- Unique process applied for the whole germanium bulk
- · Probability of failure is minimal, no need for ion pump
- · High electromagnetics immunity even in harsh environments
- Modular removable electronics for easy on-site maintenance

MINIMAL FOOTPRINT CUSTOMIZATIONS

- Special configuration for Dewars such as Dewar on top, tilted Dewar
- · All attitude, compact electrical cooler
- Standard 15 L and 30 L Dewars, can be reduced down to 3 L
- · Off-axis detector heads



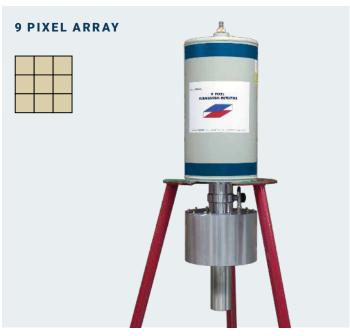
100 pixels detector in a small footprint configuration

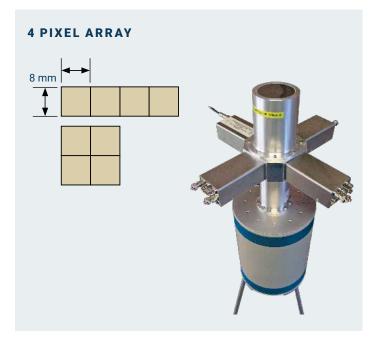




Standard Configuration Examples











Small footprint 100 pixel detector Electrically cooled detectors

TYPICAL SPECIFICATIONS FOR MONOLITHIC HPGE PIXEL DETECTOR

(Other configurations available)

- · Pixel size (mm)
 - 5 x 5 mm and 8 x 8 mm
- Thickness
 - 7 mm (X-rays) to 20 mm (gamma rays)
- Layout
 - Linear or square arrays
 - From 1 pixel to 100 pixel and more
- Energy resolution at 5.9 keV (12 μs)
 - 5 mm x 5 mm pixels: Typ <135 eV
 - 8 mm x 8 mm pixels: Typ <145 eV
- Energy resolution at 5.9 keV (0,5 μs)
 - 5 mm x 5 mm pixels: Typ <235 eV
 - 8 mm x 8 mm pixels: Typ <250 eV
- Dewar size
 - 15 L and 30 L; Electrical cooler
- · Entrance window
 - 50 μm 250 μm Beryllium
 - Low fluorescence materials
- · Front end electronics
 - Pulsed preamplifier
 - Alarm card for high temperature shutdown
- · Options
 - Square head
 - Readout electronics of the latest digitizer technology
 - Preamplifier power supply unit
 - High voltage supply unit
 - On-site installation and training, etc.

Discrete Element Array Detectors

- · 2 to 32 individual HPGe or Si(Li) elements
- · Energy range:
 - LEGe[™] detector (3 keV and up)
 - Ultra-LEGe (1 kev and up) elements
- · Low crosstalk (permitting non-synchronous or synchronous preamp reset modes)
- · High resolution even with very short pulse processing times
- · Count rates up to 1 Mcps
- · Excellent peak/background without collimation
- · Windowless cryostats available for Ultra-LEGe's detector's to achieve energy sensitivity down to 300 eV
- · Optional electrically cooled cryostat





High Count Rate Multichannel Detectors

- New generation Multichannel X-ray detectors with CMOS preamplifier
- From 1 to 25 channels available in highly customizable configurations
- Both pixelated monolithic and multiple individual crystals available
- Major breakthrough in performance compared to JFET-based detectors
 - 10x increase in throughput (up to several Mcps/channel demonstrated on synchrotron beamlines)
 - FWHM divided by two at short shaping time (typical 150 eV@6 keV and 0.125 μs)
 - Rise time divided by five (typical 35 ns/event)
- Electrical cooling for maintenance-free operation and compact footprint (water chiller option available)
- Fully compatible with new generation digital readout electronics (Xia FalconX and Quantum Xspress 3)





Double-Sided Strip Detectors

- · Interaction localization
- · HPGe or Si(Li) planar detectors
- · Particles, X and gamma radiation imaging
- · Compton camera using crystals stacked in a single cryostat
- · No measurable crosstalk effect





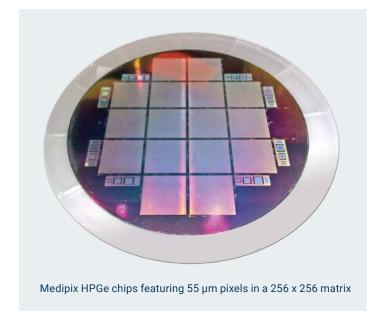
Nanofocused Beam Detectors

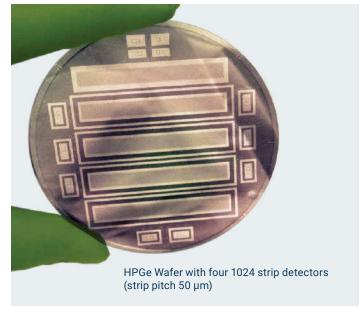
- Electrical cooling for X-ray (LN₂-free)
- Ultimate FWHM performance at low energy X-rays
- Highest throughput for count rates up to 10⁶ counts per second
- · Zero vibration: no fans needed for cooling
- No heat exchange with the hutch: water coolant circuit for the CP5-PLUS cryostat and the preamplifiers
- · Smallest footprint to fit a very limited space
- · Best immunity in a highly electromagnetic environment
- Selected material for the hardware in proximity with the U-LEGe™ diodes



Finely Pixelated GE Sensors

- · Micrometrical scale patterned HPGe wafers
- Range from mm to µm
- · Application covers medical imaging, non-destructive testing, XRD, radiography, high count rate conditions
- Down to 55 µm pixel





Single Element X-Ray Detectors

- · Low Energy Germanium (LEGe) Detectors for 3 keV and up
- Ultra Low-Energy Germanium Detectors for 1 keV and up (300 eV with windowless cryostat)
- · Lithium-Drifted Silicon (SiLi) Detectors for 1-25 keV
- X-PIPS[™] Detectors for 2-30 keV (Miniature Peltier-Cooled Devices)

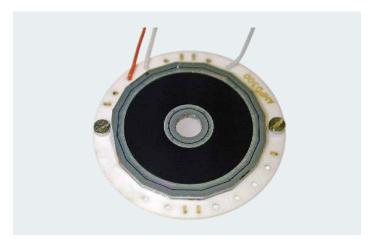


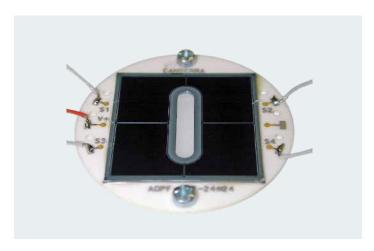


Photodiodes For Beam Alignment

- · Low dark current
- · Fast read-out
- · Used in photovoltaic or biased mode
- · No optical window







Si(Li) Detectors

Silicon Lithium Si(Li) detectors play an important role alongside Silicon detectors and HPGe detectors.

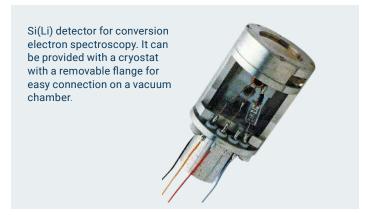
These detectors excel in the spectroscopy of X-rays, charged particles and conversion electrons. They offer optimal performance and excellent long-term reliability even in rough conditions. Si(Li) detectors can be made up to 5 mm thick, which means they have a much higher stopping power than SDD's (max. 500 μm) and can be used with higher energy X-rays. Compared to germanium, however, silicon has a lower stopping power, and thus lower efficiency, for the same detector thickness. The advantage of silicon is that it has characteristic X-rays at much lower energies (around 1.7 keV) compared to germanium (10-11 keV) and are therefore much less likely to interfere with those X-rays being studied.

- Thickness 2 mm and 5 mm (other thicknesses available on request)
- Active area 200 mm² and 500 mm² (other areas available on request)
- Available in multi-element arrays or strip detector configuration
- · Stackable for dE/dX measurements









High Count Rate Multi-Element SDD Array

The X-PIPS detector array is a spectroscopy sub-system that is sensitive to X-rays and low-energy gamma rays. It comprises of several (13 or more) Silicon Drift Detectors (SDD) with a low noise CMOS reset type preamplifier, an HV bias supply and a cryogenic cooler. The detector elements and CMOS preamplifiers are cooled and temperature regulated, ensuring stable operation in changing environmental conditions. The Beryllium entrance window is 2 mil (50 µm) thick which allows for measurement of X-rays as low as 2 keV.

The CMOS preamplifiers have a fast reset mechanism which reduces dead time and allows the detector to perform well at high count rate performance. The high performance SDD combined with a CMOS preamplifier provides a fast, low noise response, which results in optimal energy resolution with fast peaking times.

PERFORMANCE

- Collimated Active Area 30, 50 or 80 mm² per element
- Thickness 0.5 mm
- Guaranteed resolution 135 eV FWHM (typ. < 125 eV)
- Energy Range 2 to 30 keV
- Maximum throughput per element: > 3.5 Mcps
- · Peak-to-back ratio: > 10 000:1

- · 13 or more elements
- · Cryogenic (pulse-tube) cooler
- · Easily customized
- · Planar of focused configurations
- · Air or water cooled heat sink
- · No active pumping required (no ion pump)
- · Thermal cycle free



High Count Rate Multi-Element SDD Array

Examples of Custom Configurations

EXAMPLE 1

- 7 x 50 mm² collimated elements
- 1.5 W Pulse-Tube cooler
 - High reliability and long life (> 10 years)
 - Low power consumption (< 50 W)
- · Air or water cooled heat sink



EXAMPLE 2

- 7 x 80 mm² collimated elements
- 5 W Pulse-Tube cooler
 - High reliability and long life (>10 years)
- Focused arrangement
- Air or water cooled heat sink



EXAMPLE 3

- 8 x 80 mm² collimated elements
- · Focused arrangement





Mirion Technologies provides products and services for a wide range of radiation safety, measurement and scientific purposes.

Mirion solutions are employed to protect people from radiation exposure and limit the spread of contamination. Since 1968, the company has also been committed to the development, manufacturing and service of unique specialty detectors for international scientific experiments, as well as industrial applications.

Driven by the diverse needs of our customers, Mirion has developed a range of solutions to maintain its technological leadership in the nuclear measurements industry.

Mirion supplies detectors and instrumentation used in laboratory and in-situ radiological analysis, and for cuttingedge materials analysis, physics, and space studies in some of the world's leading research institutes.

Our dedicated R&D structure allows us to deliver innovative nuclear detection systems based on a comprehensive exploration of all available and emerging technologies.

Our passion for fully understanding the needs of our customers is key to our ability to provide the best solutions to contribute to their success.

Mirion Services augments your technical team, assists during peak periods, provides expert advice, trains staff and maintains your systems for optimal performance. We look forward to partnering with you.





Empowering Progress Across Continents

Mirion Technologies combines innovative radiation safety technologies with unrivaled expertise, cultivated over decades of collaboration with reactor manufacturers and operators, nuclear fuel facilities, regulators, national labs (such as the U.S. DOE), nuclear institutes, universities, and national military/security organizations worldwide.

Trust us to provide the solutions and support you need to safeguard your valuable assets and ensure a secure and sustainable future.

CORPORATE HQ (ATLANTA, GA) MANUFACTURING SITES SERVICE & SALES CENTERS

EUROPE

2,700 PEOPLE IN 12 COUNTRIES

Local contacts

Mirion Technologies (Canberra Olen) NV Lammerdries-Oost 25

Lammerdries-Oost 25 B-2250 OLEN Belgium

Mirion Technologies (Canberra) France SAS

1 chemin de la Roseraie – Parc des Tanneries BP 10056 - 67382 LINGOLSHEIM CEDEX France Mirion Technologies (Canberra), Inc. 800 Research Parkway Meriden, CT 06450 USA





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